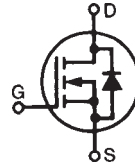


Polar™ Power MOSFET

HiPerFET™

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

IXFN40N110P

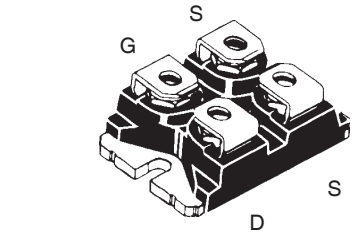


$$\begin{aligned} V_{DSS} &= 1100V \\ I_{D25} &= 34A \\ R_{DS(on)} &\leq 260m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1100	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1100	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	34	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	100	A
I_{AR}	$T_C = 25^\circ C$	20	A
E_{AS}	$T_C = 25^\circ C$	2	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	20	V/ns
P_D	$T_C = 25^\circ C$	890	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
V_{ISOL}	50/60 Hz, RMS	t = 1min	2500 V~
	$I_{ISOL} \leq 1mA$	t = 1s	3000 V~
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque	1.3/11.5	Nm/lb.in.
Weight		30	g

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	1100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1mA$	3.5		6.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 300 nA
I_{DSS}	$V_{DS} = V_{DSS}$			50 μA
	$V_{GS} = 0V$, $T_J = 125^\circ C$			3 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 20A$, Note 1			260 m Ω

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source
D = Drain

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance - easy to drive and to protect

Advantages

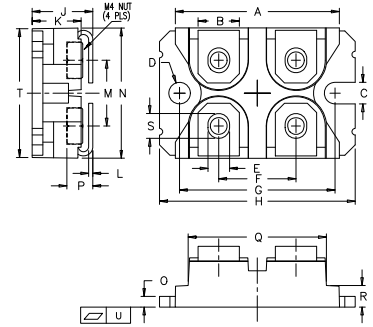
- Easy to mount
- Space savings
- High power density

Applications:

- High Voltage Switched-mode and resonant-mode power supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC converters
- High Voltage DC-AC inverters

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 20\text{A}, \text{ Note 1}$	20	32	S
R_{Gi}	Gate input resistance		1.65	Ω
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		19	nF
C_{oss}			1070	pF
C_{rss}			46	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 20\text{A}$ $R_G = 1\Omega$ (External)		53	ns
t_r			55	ns
$t_{d(off)}$			110	ns
t_f			54	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 20\text{A}$		310	nC
Q_{gs}			95	nC
Q_{gd}			142	nC
R_{thJC}				0.14 $^\circ\text{C/W}$
R_{thCS}			0.05	$^\circ\text{C/W}$

Source-Drain Diode		Characteristic Values		
$T_J = 25^\circ\text{C}$ unless otherwise specified)		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			40 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			160 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}, \text{ Note 1}$			1.5 V
t_{rr}	$I_F = 20\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
Q_{RM}			2.2	μC
I_{RM}			16	A

SOT-227B Outline


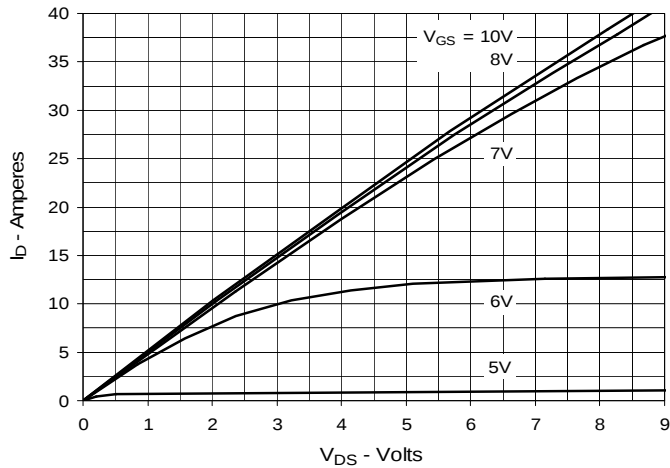
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

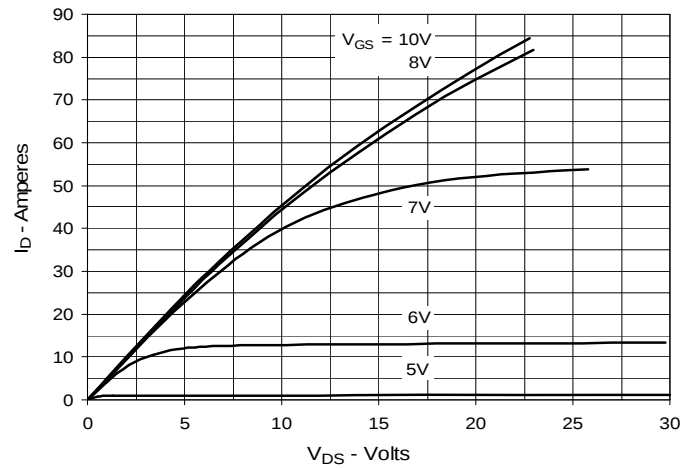
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

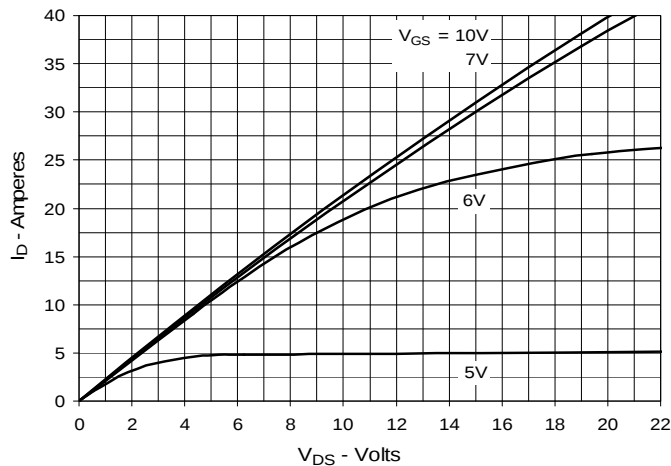
**Fig. 1. Output Characteristics
@ 25°C**



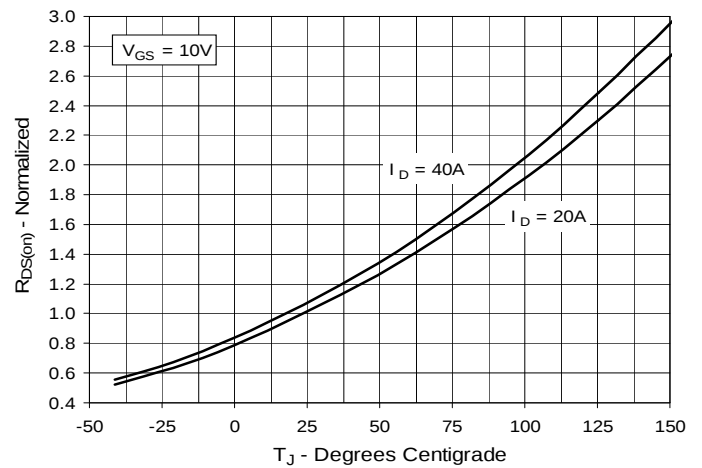
**Fig. 2. Extended Output Characteristics
@ 25°C**



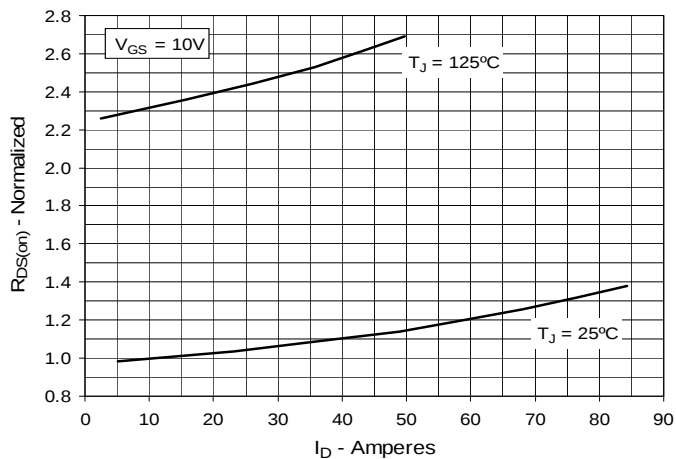
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 20A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 20A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

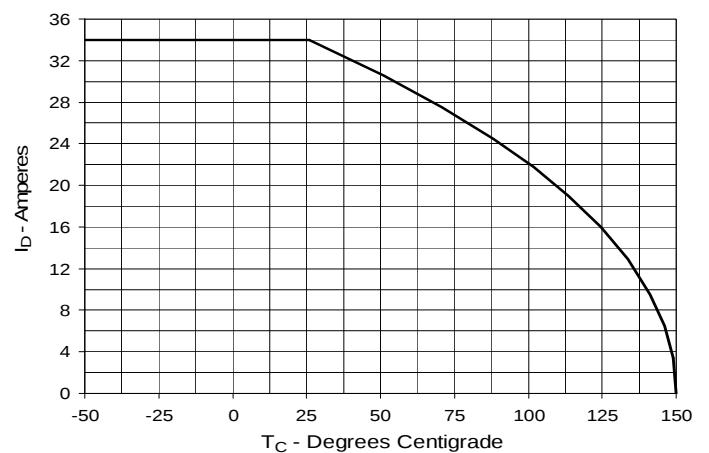
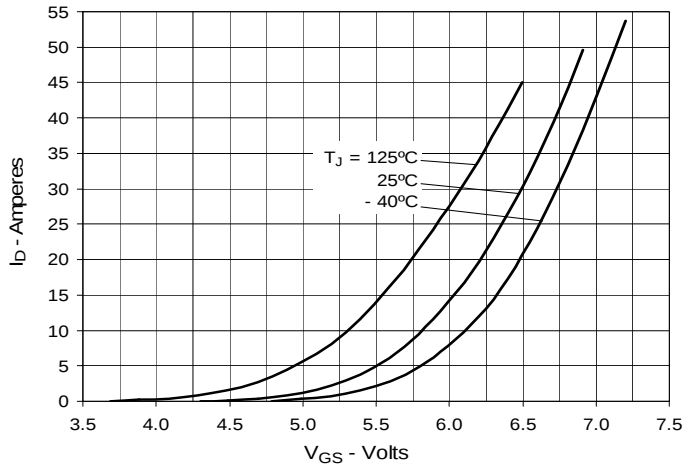
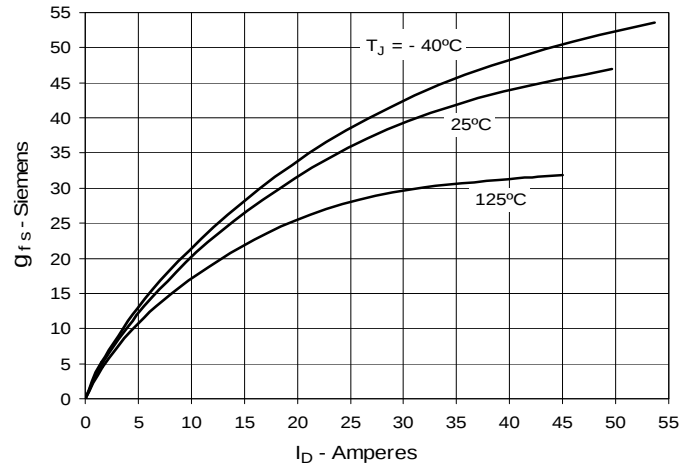
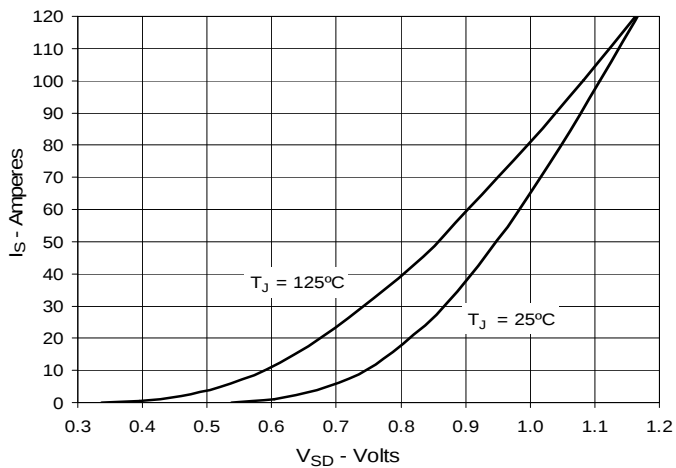
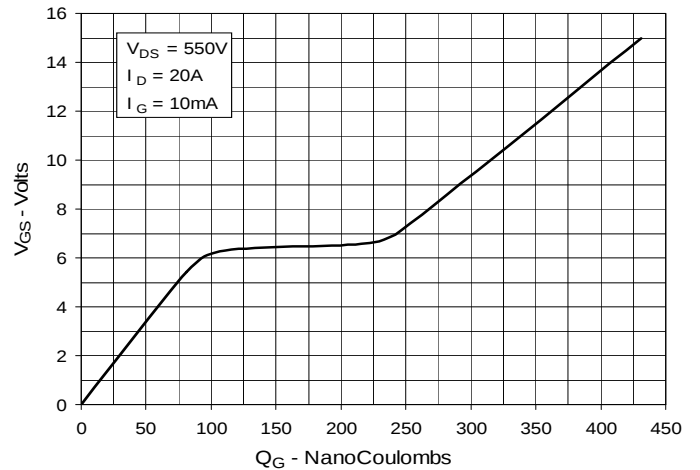
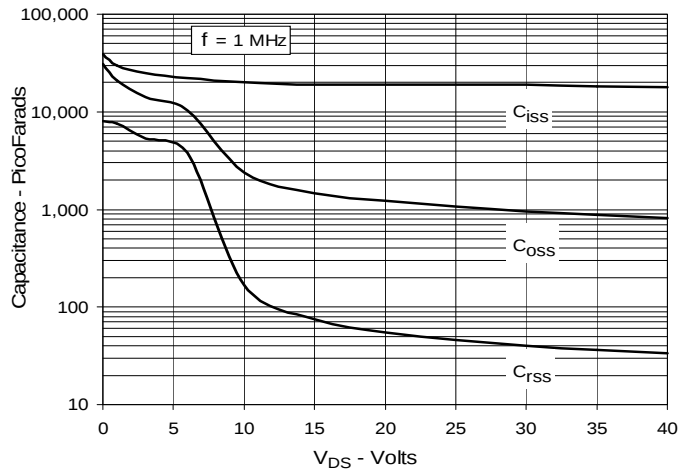


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance
